

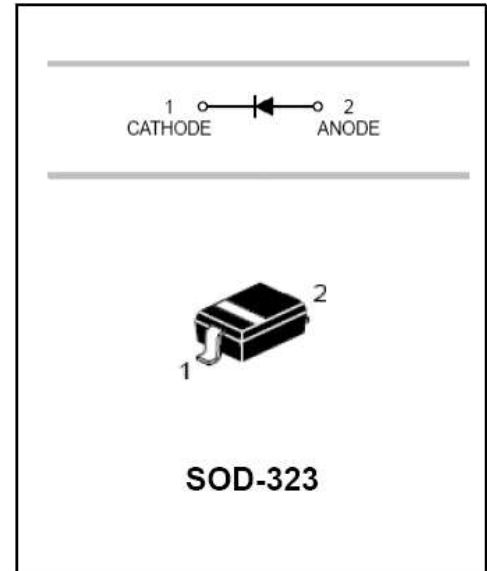
## Schottky Barrier Diode

### FEATURES

- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.

### APPLICATIONS

- Schottky barrier switching.



### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol		Unit
Peak Repetitive Peak reverse voltage	$V_{RR}$		
Working Peak DC Reverse Voltage	$V_{RWM}$	30	V
	$V_R$		
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	$I_F$	150	mA
Repetitive Peak Forward Current @t≤1.0s	$I_{FRM}$	1.5	A
Power Dissipation	$P_d$	400	mW
Thermal Resistance Junction to Ambient	$R_{\theta jA}$	300	°C/W
Storage temperature	$T_{stg}$	-65~+125	°C

## ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	30			V	$I_R=10\mu A$
Forward voltage	$V_F$			0.4 0.8	V	$I_F=20mA$ $I_F=200mA$
Reverse current	$I_{RM}$			5.0	$\mu A$	$V_R=30V$ $V_R=20V$ $V_R=10V$
Capacitance between terminals	$C_T$		50		pF	$V_R=0, f=1MHz$
Reverse Recovery Time	$t_{rr}$		10		ns	$I_R=I_F=200mA$ $I_{rr}=0.1 \cdot I_R, R_L=100\Omega$

## TYPICAL CHARACTERISTICS

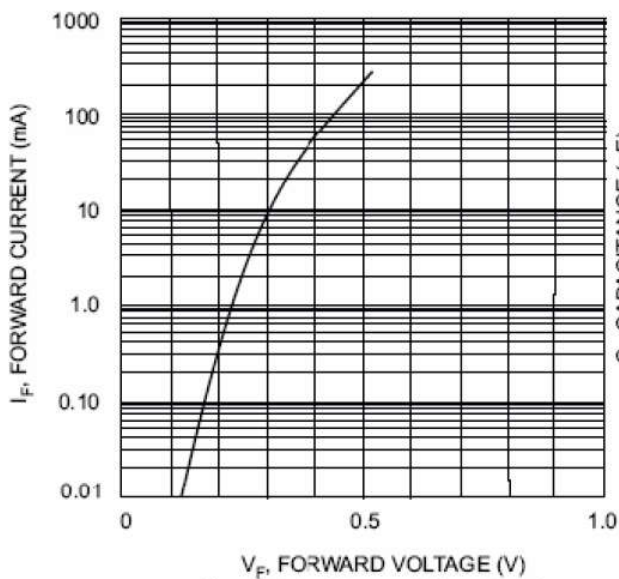


Fig. 1 Typical Forward Characteristics

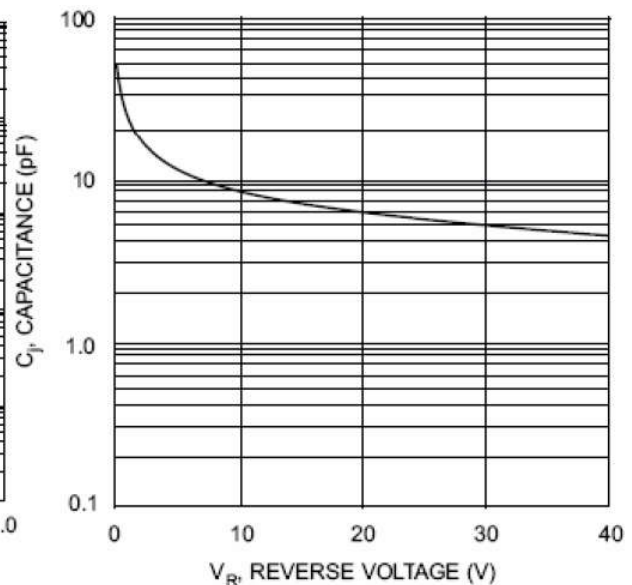


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage